



EDS 2024 - Was it worth it?



This year's EDS conference was certainly a challenge with a new venue, a change in date and attendance uncertainty. However, the EDS management team met the challenge head on and executed an outstanding event. In the 3 days of the event, Central held 22 meetings in our suite with both our manufacturer's representatives and our key distributors. Overall, there was a positive feeling that the industry is at the bottom of the downturn and foresee an upturn at the start of 2025. The Central team presented the 2024/2025 strategic plan with an even further view out to 2027 with exciting new innovative devices, rapid design and development program and additional up-screening and other services. Thank you to all who participated.

Innovative Solutions for your Design Challenges

Central Semiconductor is dedicated to solving our customers' most relevant design challenges with innovative and responsive solutions. From a package or dimension change to a parametric electrical screening to a semi-custom new design, Central is here to assist with a host of products and services to meet these challenges head on.



Successes: #182

Challenge

OEM was experiencing extreme failure rates due to issues caused by a highly moisture sensitive environment. Rework expenses were affecting the bottom line and brand reputation.

Solution

Central's product design team developed a solution removing all Silver from the effected component, changing the internal die attach and modifying wire bond materials. The end result is that Central delivered a failure free solution in an extremely short completion time.

If you have a challenge and need support, contact one of our sales representatives to schedule an interactive consultation with one of our product development engineers. Start on your road to your own success story.

Contact Our Team

Designer's Choice



100V, 60A N-channel GaN FET

Central's new CCSPG1060N is a 100V, 60A N-channel gallium nitride field effect transistor in a low-profile chip-scale package that is designed for use in EV charging stations, microinverters, and highly efficient fast-charging power blocks. This low voltage GaN FET meets designers' requests for a small but powerful device with high performance efficiency including low Gate charge of 9.2nC and low rDS(ON) of 5.5mΩ.

Learn More



EXPAND YOUR POSSIBILITIES

PROTECT

POWER

CONNECT



Circuit protection for, aerospace & defense, applications



Standard & semi-custom packaged & bare die discrete semiconductor solutions



HF to Millimeter Wave Components to Sub-Systems Aerospace & Defense



Circuit protection for industrial, automotive & commercial applications



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